

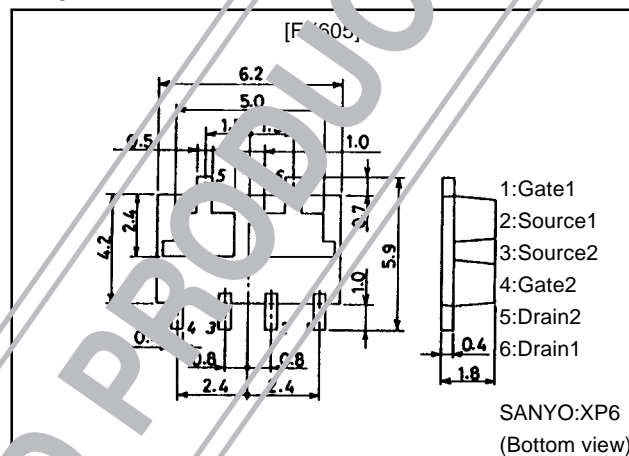
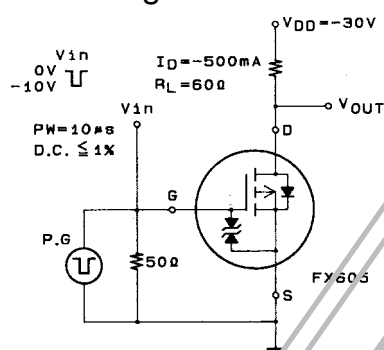
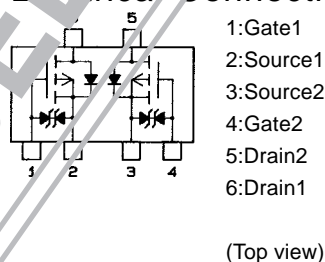
**SANYO****FX605****P-Channel Silicon MOSFET****Ultrahigh-Speed Switching Applications****Features**

- Composite type composed of two low ON-resistance P-channel MOSFET chips for ultrahigh-speed switching and low-voltage drive.
- Facilitates high-density mounting.
- The FX605 is formed with two chips, each being equivalent to the 2SJ190, placed in one package.
- Matched pair characteristics.

**Package Dimensions**

unit:mm

2120

**Switching Time Test Circuit****Electrical Connection****Specifications**Absolute Maximum Ratings at T<sub>a</sub> = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DS</sub>		-60	V
Gate-to-Source Voltage	V <sub>GS</sub>		±15	V
Drain Current (DC)	I <sub>D</sub>		-1	A
Drain Current (Pulse)	I <sub>DP</sub>	PW≤10μs, duty cycle≤1%	-4	A
Allowable Power Dissipation	P <sub>D</sub>	T <sub>c</sub> =25°C, 1unit	6	W
		Mounted on ceramic board (750mm <sup>2</sup> ×0.8mm) 1unit	1.5	W
Total Dissipation	P <sub>T</sub>	Mounted on ceramic board (750mm <sup>2</sup> ×0.8mm)	2	W
Channel Temperature	T <sub>ch</sub>		150	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C

· Marking:605

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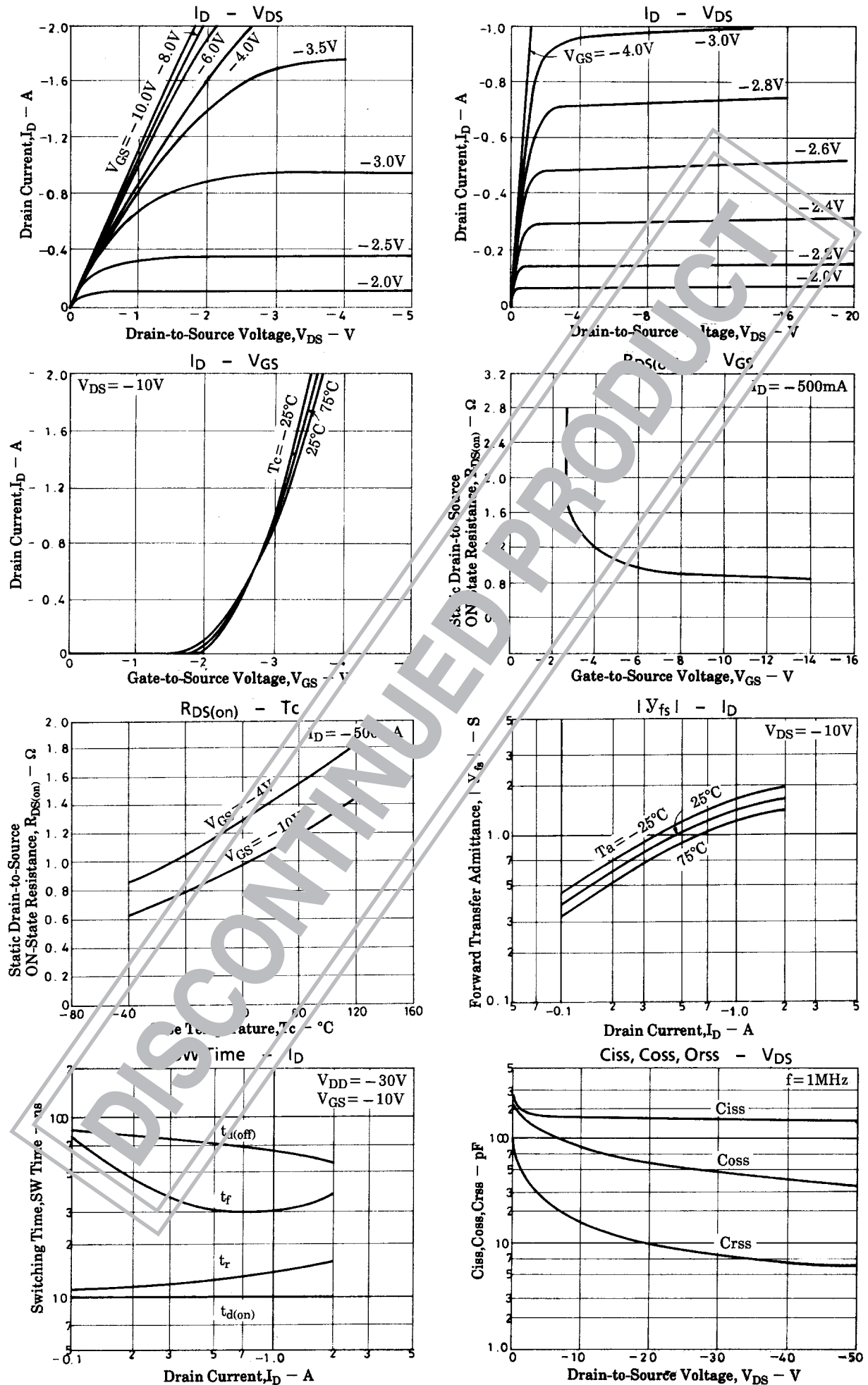
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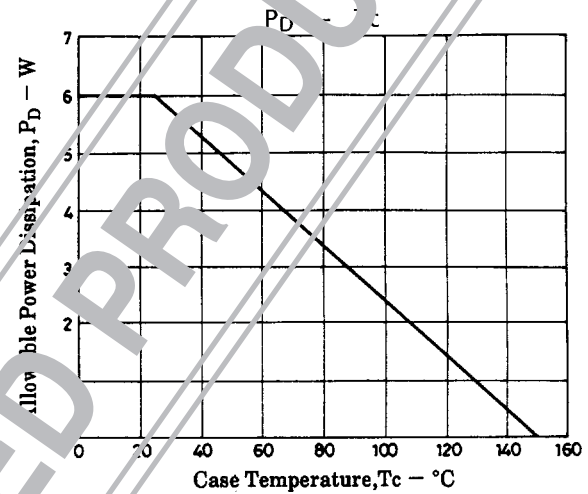
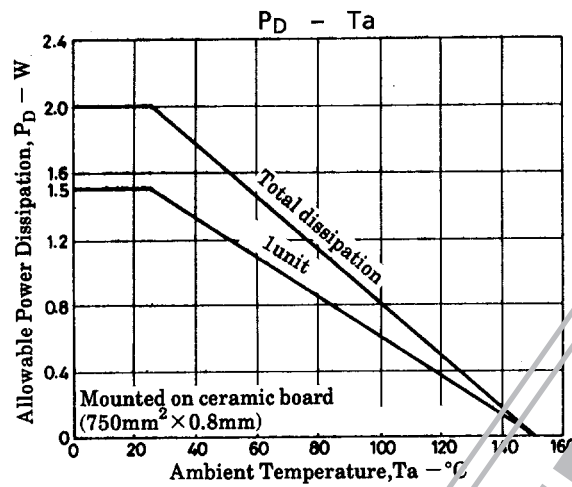
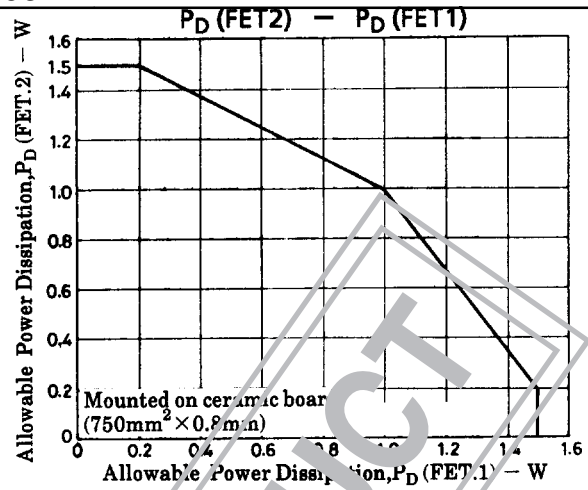
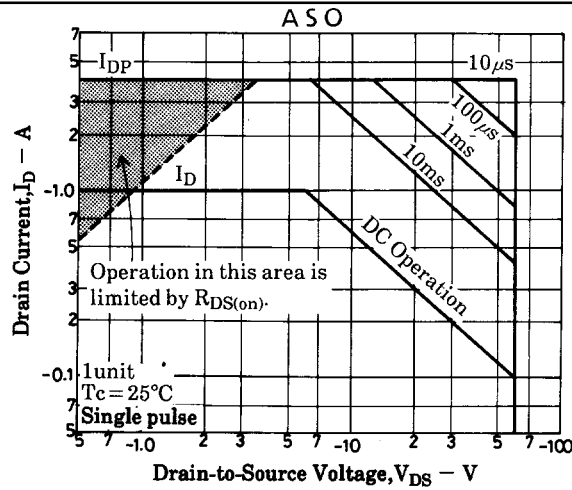
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Electrical Characteristics at  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1\text{mA}$ , $V_{GS} = 0$	-50			V
Zero-Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -60\text{V}$ , $V_{GS} = 0$			-100	$\mu\text{A}$
Gate-to-Source Leakage Current	$I_{GSS}$	$V_{GS} = \pm 12$ , $V_{DS} = 0$			$\pm 10$	$\mu\text{A}$
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10\text{V}$ , $I_D = -1\text{mA}$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10\text{V}$ , $I_D = -500\text{mA}$	0	1.0		S
Static Drain-to-Source ON-State Resistance	$R_{DS(on)}$	$I_D = -500\text{mA}$ , $V_{GS} = -10\text{V}$		0.9	1.2	$\Omega$
	$R_{DS(on)}$	$I_D = -500\text{mA}$ , $V_{GS} = -4\text{V}$		1.2	1.6	$\Omega$
Input Capacitance	$C_{iss}$	$V_{DS} = -20\text{V}$ , $f = 1\text{MHz}$		160		pF
Output Capacitance	$C_{oss}$	$V_{DS} = -20\text{V}$ , $f = 1\text{MHz}$		60		pF
Reverse Transfer Capacitance	$C_{rss}$	$V_{DS} = -20\text{V}$ , $f = 1\text{MHz}$		10		pF
Turn-ON Delay Time	$t_{d(on)}$	See Specified Test Circuit		10		ns
Rise Time	$t_r$	See Specified Test Circuit		13		ns
Turn-OFF Delay Time	$t_{d(off)}$	See Specified Test Circuit		70		ns
Fall Time	$t_f$	See Specified Test Circuit		30		ns
Diode Forward Voltage	$V_{SD}$	$I_S = -1\text{A}$ , $V_{GS} = 0$		-0.9		V

DISCONTINUED PRODUCT





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